

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
30V	14m $\Omega$ @ $V_{GS} = 10\text{V}$	8.0A
	20m $\Omega$ @ $V_{GS} = 4.5\text{V}$	6.7A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

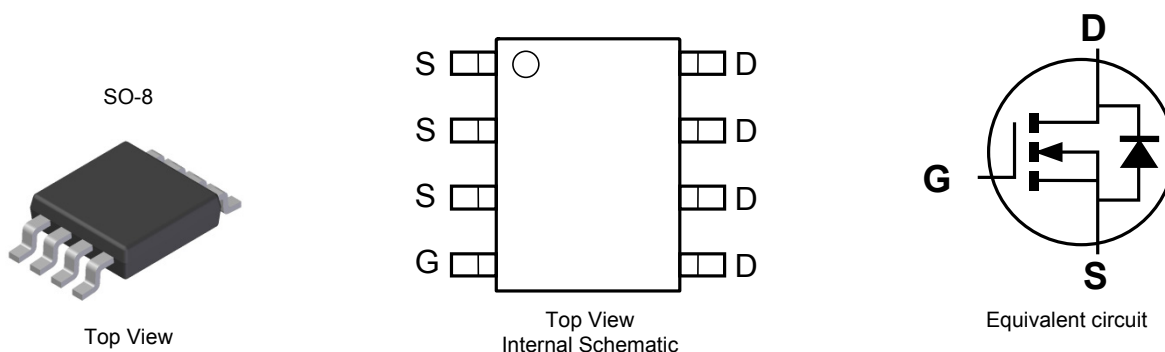
- DC-DC Converters
- Power management functions

## Features and Benefits

- 14m $\Omega$  @  $V_{GS} = 10\text{V}$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (approximate)

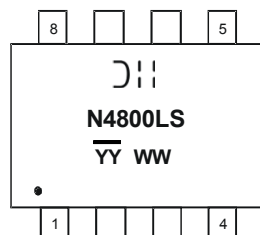


## Ordering Information (Note 4)

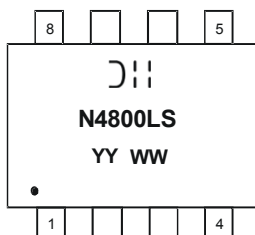
Part Number	Case	Packaging
DMN4800LSSL-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

⌋|| = Manufacturer's Marking  
 N4800LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 13 = 2013)  
 WW = Week (01 - 53)  
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V <sub>DSS</sub>	30	V
Gate-Source Voltage				V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	8.0	A
			T <sub>A</sub> = +70°C		6.4	
Drain Current (Note 5)	V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	6.7	A
			T <sub>A</sub> = +70°C		5.3	
Pulsed Drain Current (Note 6)				I <sub>DM</sub>	50	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.46	W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	86	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	1.2	1.6	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	11	14	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A
			14	20		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A
Forward Transconductance	g <sub>fs</sub>	—	8	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 8A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.72	0.94	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	798	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	128	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	122	—	pF	
Gate Resistance	R <sub>G</sub>	—	1.37	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	8.7	—	nC	V <sub>GS</sub> = 5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 9A
Gate-Source Charge	Q <sub>gs</sub>	—	1.7	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.4	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	5.03	—	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V, R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6.0Ω, I <sub>D</sub> = 1A
Rise Time	t <sub>r</sub>	—	4.50	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	26.33	—		
Fall Time	t <sub>f</sub>	—	8.55	—		

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Repetitive rating, pulse width limited by junction temperature.
  7. Short duration pulse test used to minimize self-heating effect.

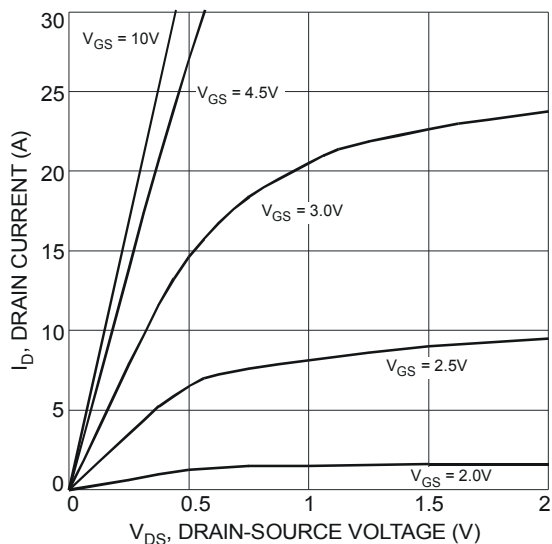


Fig. 1 Typical Output Characteristic

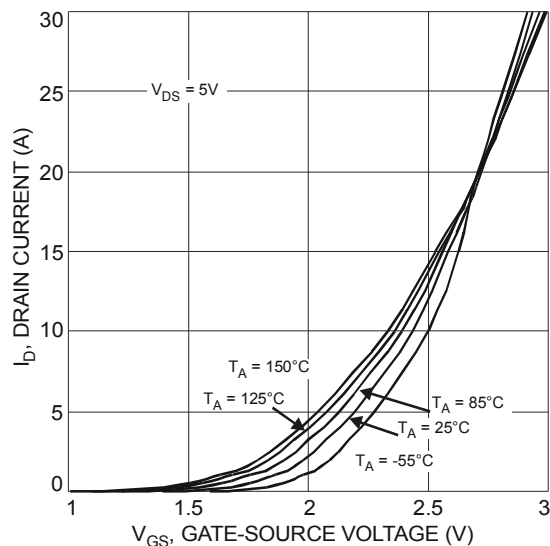


Fig. 2 Typical Transfer Characteristic

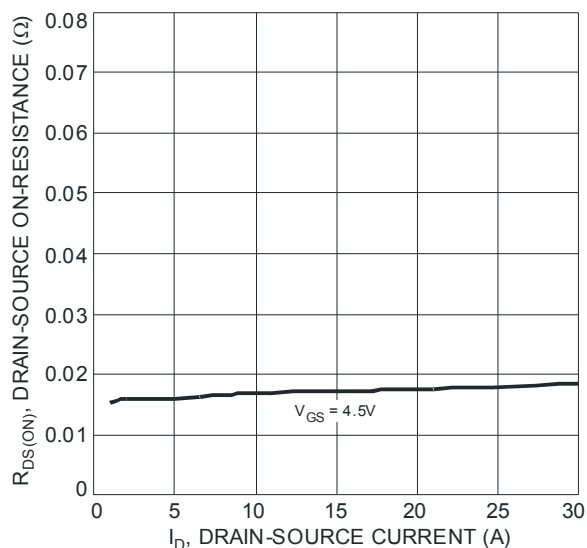


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

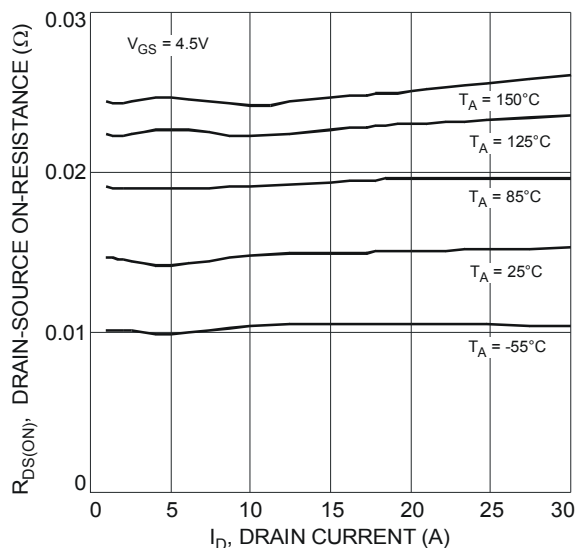


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

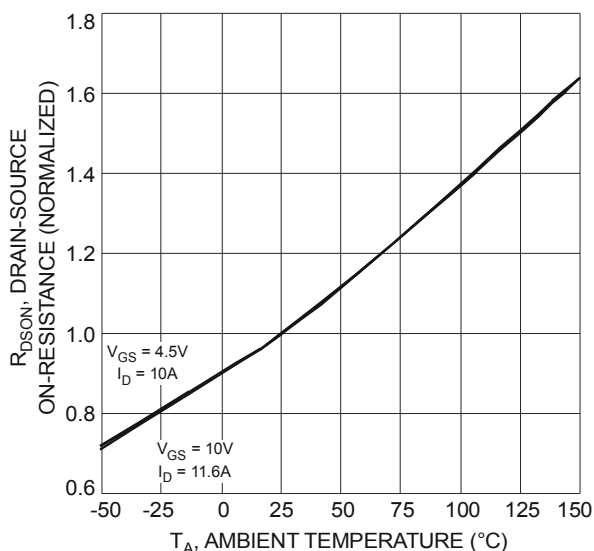


Fig. 5 On-Resistance Variation with Temperature

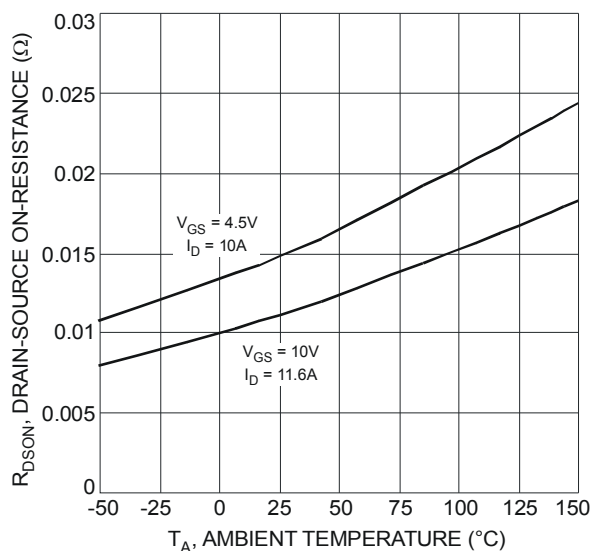


Fig. 6 On-Resistance Variation with Temperature

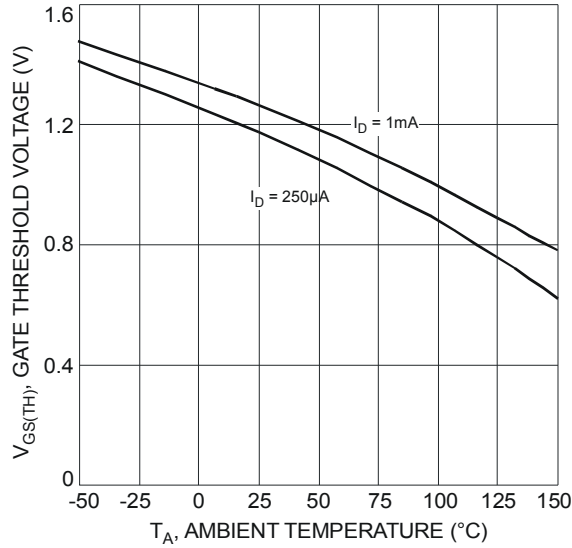


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

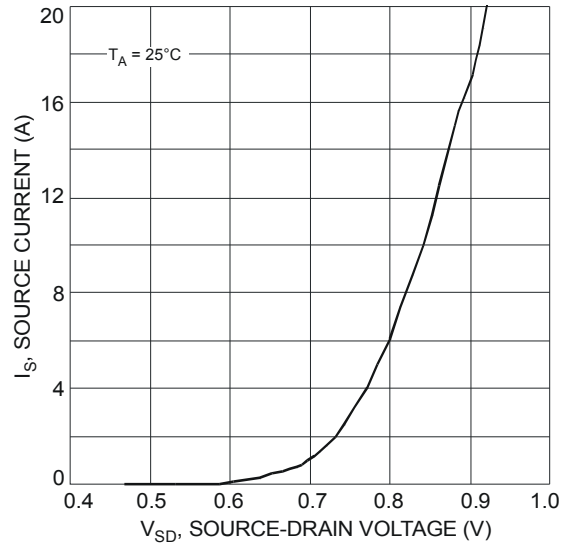


Fig. 8 Diode Forward Voltage vs. Current

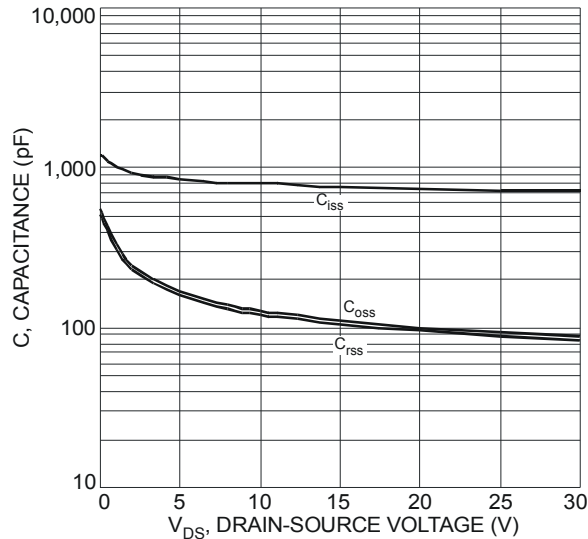


Fig. 9 Typical Total Capacitance

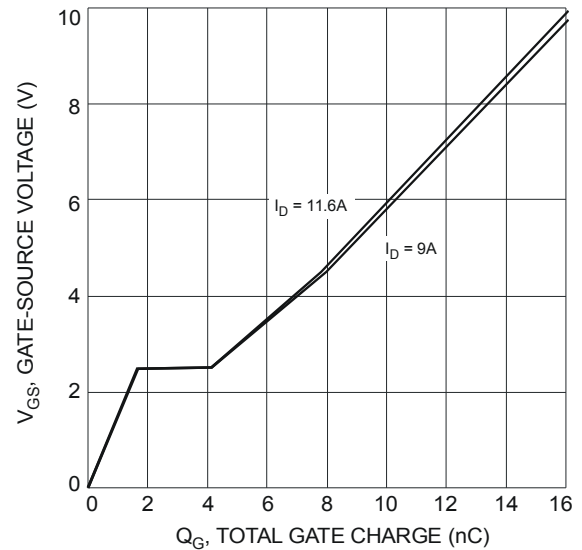


Fig. 10 Total Gate Charge

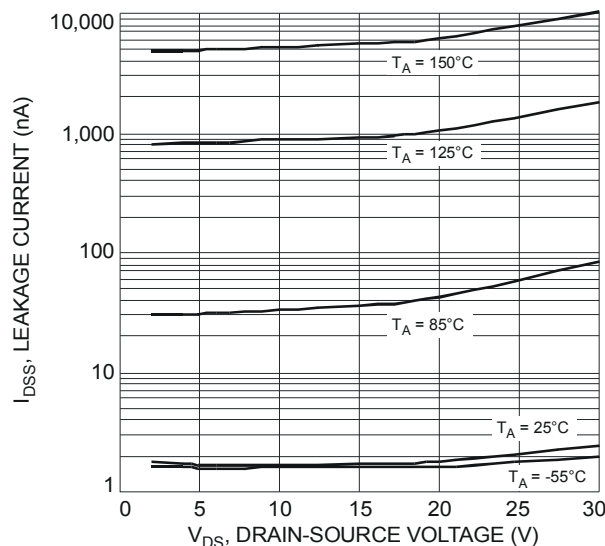


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage

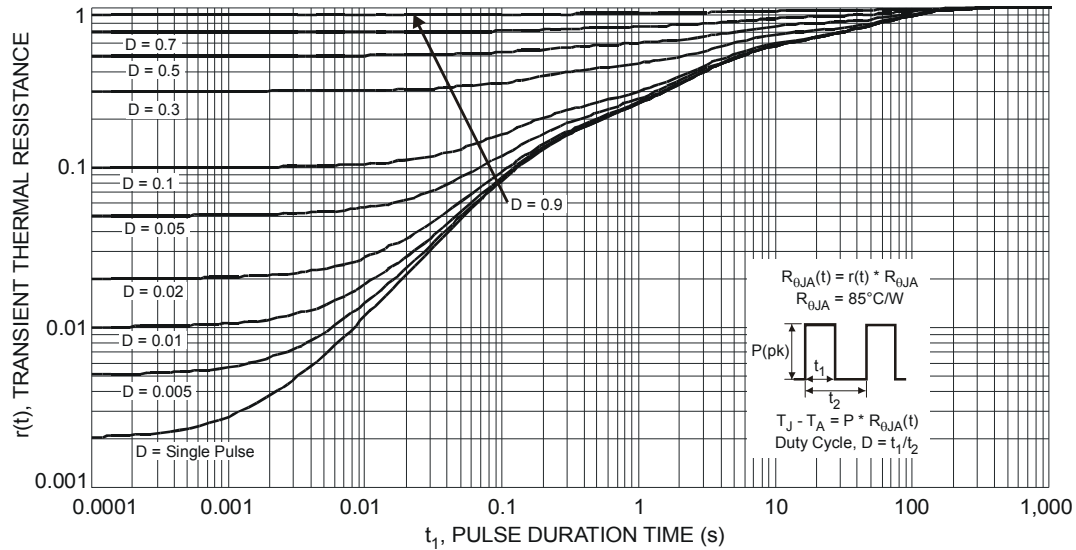
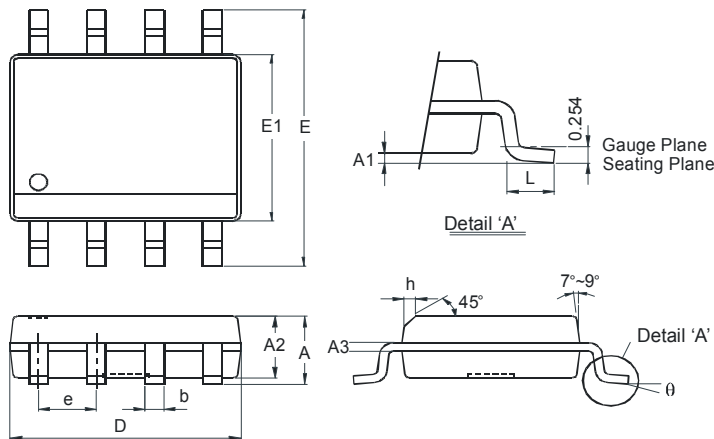


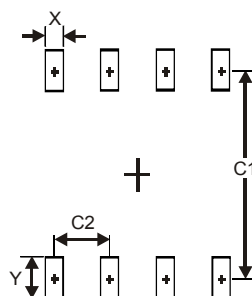
Fig. 12 Transient Thermal Response

## Package Outline Dimensions

 Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.


SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

## Suggested Pad Layout

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.


Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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